Welcome to E-XFL.COM

Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details	
Product Status	Obsolete
Number of LABs/CLBs	416
Number of Logic Elements/Cells	4160
Total RAM Bits	53248
Number of I/O	92
Number of Gates	263000
Voltage - Supply	1.71V ~ 1.89V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 85°C (TJ)
Package / Case	144-LQFP
Supplier Device Package	144-TQFP (20x20)
Purchase URL	https://www.e-xfl.com/product-detail/intel/ep20k100etc144-2

Table 5. APEX 20K FineLine BGA Package Options & I/O Count *Notes (1), (2)*

Device	144 Pin	324 Pin	484 Pin	672 Pin	1,020 Pin
EP20K30E	93	128			
EP20K60E	93	196			
EP20K100		252			
EP20K100E	93	246			
EP20K160E			316		
EP20K200			382		
EP20K200E			376	376	
EP20K300E				408	
EP20K400				502 *(3)*	
EP20K400E				488 *(3)*	
EP20K600E				508 *(3)*	588
EP20K1000E				508 *(3)*	708
EP20K1500E					808

Notes to Tables 4 and 5:

(1) I/O counts include dedicated input and clock pins.

(2) APEX 20K device package types include thin quad flat pack (TQFP), plastic quad flat pack (PQFP), power quad flat pack (RQFP), 1.27-mm pitch ball-grid array (BGA), 1.00-mm pitch FineLine BGA, and pin-grid array (PGA) packages.

(3) This device uses a thermally enhanced package, which is taller than the regular package. Consult the *Altera Device Package Information Data Sheet* for detailed package size information.

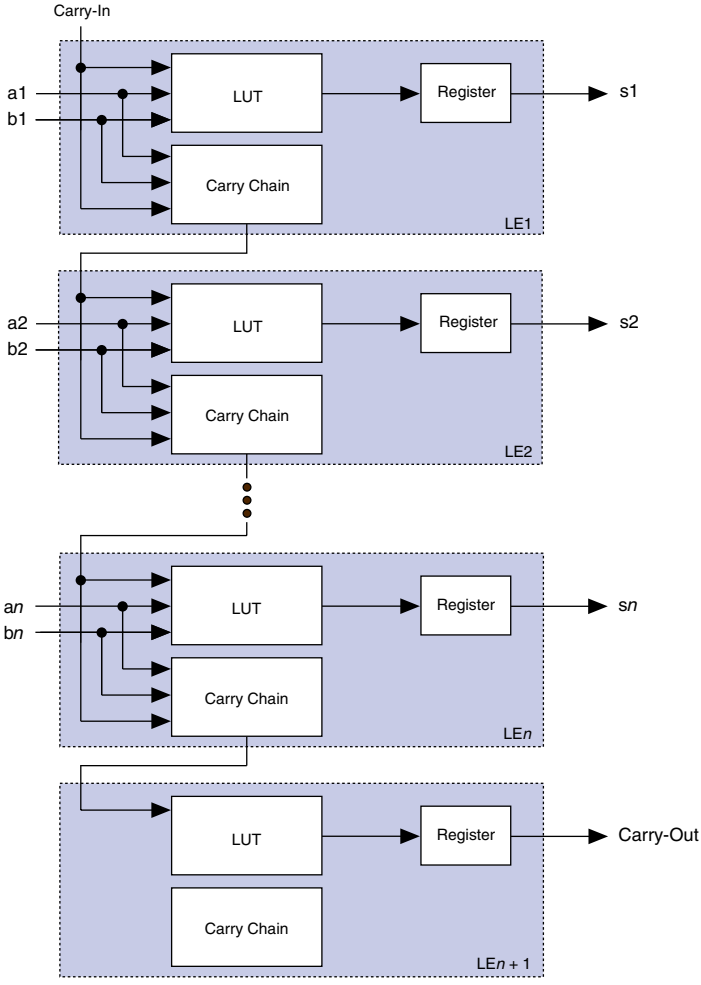
Table 6. APEX 20K QFP, BGA & PGA Package Sizes

Feature	144-Pin TQFP	208-Pin QFP	240-Pin QFP	356-Pin BGA	652-Pin BGA	655-Pin PGA
Pitch (mm)	0.50	0.50	0.50	1.27	1.27	–
Area (mm^2)	484	924	1,218	1,225	2,025	3,906
Length × Width (mm × mm)	22 × 22	30.4 × 30.4	34.9 × 34.9	35 × 35	45 × 45	62.5 × 62.5

Table 7. APEX 20K FineLine BGA Package Sizes

Feature	144 Pin	324 Pin	484 Pin	672 Pin	1,020 Pin
Pitch (mm)	1.00	1.00	1.00	1.00	1.00
Area (mm^2)	169	361	529	729	1,089
Length × Width (mm × mm)	13 × 13	19 × 19	23 × 23	27 × 27	33 × 33

Figure 6. APEX 20K Carry Chain



The counter mode uses two three-input LUTs: one generates the counter data, and the other generates the fast carry bit. A 2-to-1 multiplexer provides synchronous loading, and another AND gate provides synchronous clearing. If the cascade function is used by an LE in counter mode, the synchronous clear or load overrides any signal carried on the cascade chain. The synchronous clear overrides the synchronous load. LEs in arithmetic mode can drive out registered and unregistered versions of the LUT output.

Clear & Preset Logic Control

Logic for the register's clear and preset signals is controlled by LAB-wide signals. The LE directly supports an asynchronous clear function. The Quartus II software Compiler can use a NOT-gate push-back technique to emulate an asynchronous preset. Moreover, the Quartus II software Compiler can use a programmable NOT-gate push-back technique to emulate simultaneous preset and clear or asynchronous load. However, this technique uses three additional LEs per register. All emulation is performed automatically when the design is compiled. Registers that emulate simultaneous preset and load will enter an unknown state upon power-up or when the chip-wide reset is asserted.

In addition to the two clear and preset modes, APEX 20K devices provide a chip-wide reset pin (DEV_CLRn) that resets all registers in the device. Use of this pin is controlled through an option in the Quartus II software that is set before compilation. The chip-wide reset overrides all other control signals. Registers using an asynchronous preset are preset when the chip-wide reset is asserted; this effect results from the inversion technique used to implement the asynchronous preset.

FastTrack Interconnect

In the APEX 20K architecture, connections between LEs, ESBs, and I/O pins are provided by the FastTrack Interconnect. The FastTrack Interconnect is a series of continuous horizontal and vertical routing channels that traverse the device. This global routing structure provides predictable performance, even in complex designs. In contrast, the segmented routing in FPGAs requires switch matrices to connect a variable number of routing paths, increasing the delays between logic resources and reducing performance.

The FastTrack Interconnect consists of row and column interconnect channels that span the entire device. The row interconnect routes signals throughout a row of MegaLAB structures; the column interconnect routes signals throughout a column of MegaLAB structures. When using the row and column interconnect, an LE, IOE, or ESB can drive any other LE, IOE, or ESB in a device. See Figure 9.

Table 9. APEX 20K Routing Scheme

Source	Destination								
	Row I/O Pin	Column I/O Pin	LE	ESB	Local Interconnect	MegaLAB Interconnect	Row FastTrack Interconnect	Column FastTrack Interconnect	FastRow Interconnect
Row I/O Pin					✓	✓	✓	✓	
Column I/O Pin								✓	✓ (1)
LE					✓	✓	✓	✓	
ESB					✓	✓	✓	✓	
Local Interconnect	✓	✓	✓	✓					
MegaLAB Interconnect					✓				
Row FastTrack Interconnect						✓		✓	
Column FastTrack Interconnect						✓	✓		
FastRow Interconnect					✓ (1)				

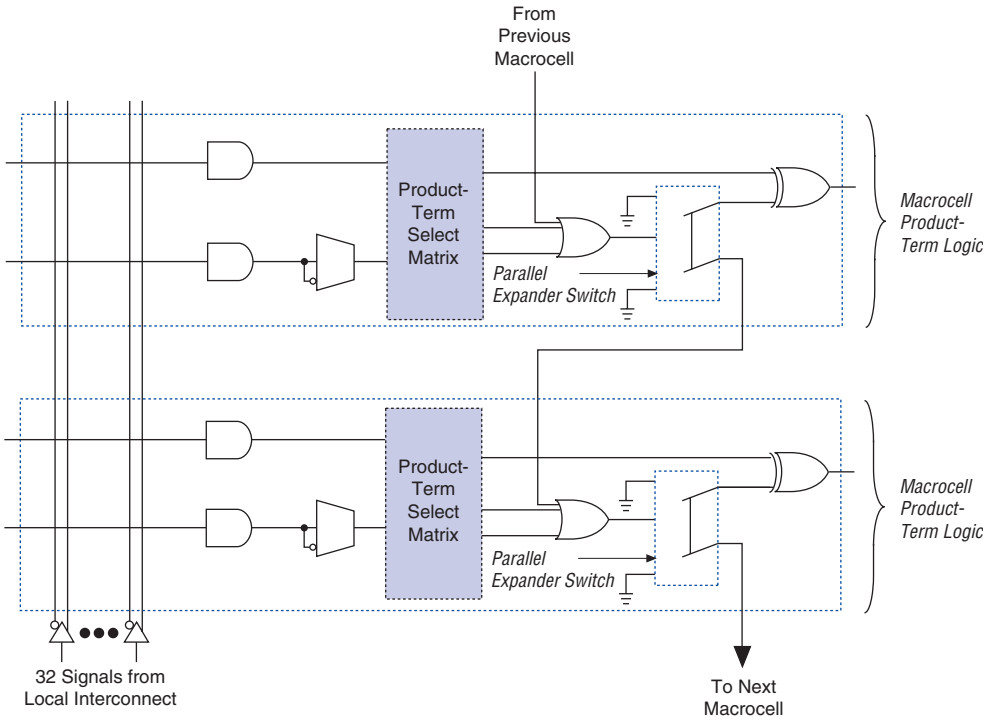
Note to Table 9:
(1) This connection is supported in APEX 20KE devices only.

Product-Term Logic

The product-term portion of the MultiCore architecture is implemented with the ESB. The ESB can be configured to act as a block of macrocells on an ESB-by-ESB basis. Each ESB is fed by 32 inputs from the adjacent local interconnect; therefore, it can be driven by the MegaLAB interconnect or the adjacent LAB. Also, nine ESB macrocells feed back into the ESB through the local interconnect for higher performance. Dedicated clock pins, global signals, and additional inputs from the local interconnect drive the ESB control signals.

In product-term mode, each ESB contains 16 macrocells. Each macrocell consists of two product terms and a programmable register. Figure 13 shows the ESB in product-term mode.

Figure 16. APEX 20K Parallel Expanders



Embedded System Block

The ESB can implement various types of memory blocks, including dual-port RAM, ROM, FIFO, and CAM blocks. The ESB includes input and output registers; the input registers synchronize writes, and the output registers can pipeline designs to improve system performance. The ESB offers a dual-port mode, which supports simultaneous reads and writes at two different clock frequencies. Figure 17 shows the ESB block diagram.

Figure 17. ESB Block Diagram

ESBs can implement synchronous RAM, which is easier to use than asynchronous RAM. A circuit using asynchronous RAM must generate the RAM write enable (WE) signal, while ensuring that its data and address signals meet setup and hold time specifications relative to the WE signal. In contrast, the ESB's synchronous RAM generates its own WE signal and is self-timed with respect to the global clock. Circuits using the ESB's self-timed RAM must only meet the setup and hold time specifications of the global clock.

ESB inputs are driven by the adjacent local interconnect, which in turn can be driven by the MegaLAB or FastTrack Interconnect. Because the ESB can be driven by the local interconnect, an adjacent LE can drive it directly for fast memory access. ESB outputs drive the MegaLAB and FastTrack Interconnect. In addition, ten ESB outputs, nine of which are unique output lines, drive the local interconnect for fast connection to adjacent LEs or for fast feedback product-term logic.

When implementing memory, each ESB can be configured in any of the following sizes: 128 × 16, 256 × 8, 512 × 4, 1,024 × 2, or 2,048 × 1. By combining multiple ESBs, the Quartus II software implements larger memory blocks automatically. For example, two 128 × 16 RAM blocks can be combined to form a 128 × 32 RAM block, and two 512 × 4 RAM blocks can be combined to form a 512 × 8 RAM block. Memory performance does not degrade for memory blocks up to 2,048 words deep. Each ESB can implement a 2,048-word-deep memory; the ESBs are used in parallel, eliminating the need for any external control logic and its associated delays.

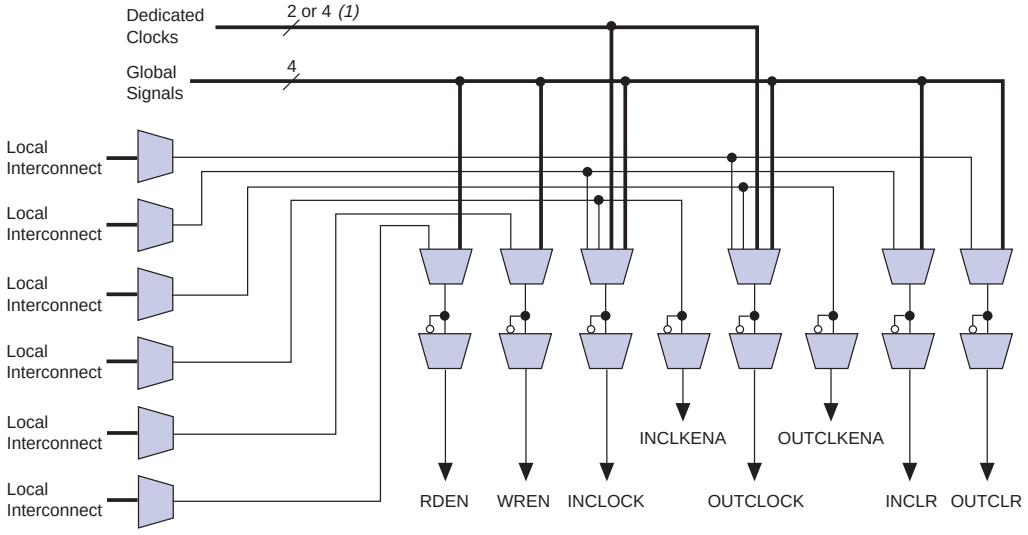
To create a high-speed memory block that is more than 2,048 words deep, ESBs drive tri-state lines. Each tri-state line connects all ESBs in a column of MegaLAB structures, and drives the MegaLAB interconnect and row and column FastTrack Interconnect throughout the column. Each ESB incorporates a programmable decoder to activate the tri-state driver appropriately. For instance, to implement 8,192-word-deep memory, four ESBs are used. Eleven address lines drive the ESB memory, and two more drive the tri-state decoder. Depending on which 2,048-word memory page is selected, the appropriate ESB driver is turned on, driving the output to the tri-state line. The Quartus II software automatically combines ESBs with tri-state lines to form deeper memory blocks. The internal tri-state control logic is designed to avoid internal contention and floating lines. See Figure 18.

For more information on APEX 20KE devices and CAM, see *Application Note 119 (Implementing High-Speed Search Applications with APEX CAM).*

Driving Signals to the ESB

ESBs provide flexible options for driving control signals. Different clocks can be used for the ESB inputs and outputs. Registers can be inserted independently on the data input, data output, read address, write address, WE, and RE signals. The global signals and the local interconnect can drive the WE and RE signals. The global signals, dedicated clock pins, and local interconnect can drive the ESB clock signals. Because the LEs drive the local interconnect, the LEs can control the WE and RE signals and the ESB clock, clock enable, and asynchronous clear signals. Figure 24 shows the ESB control signal generation logic.

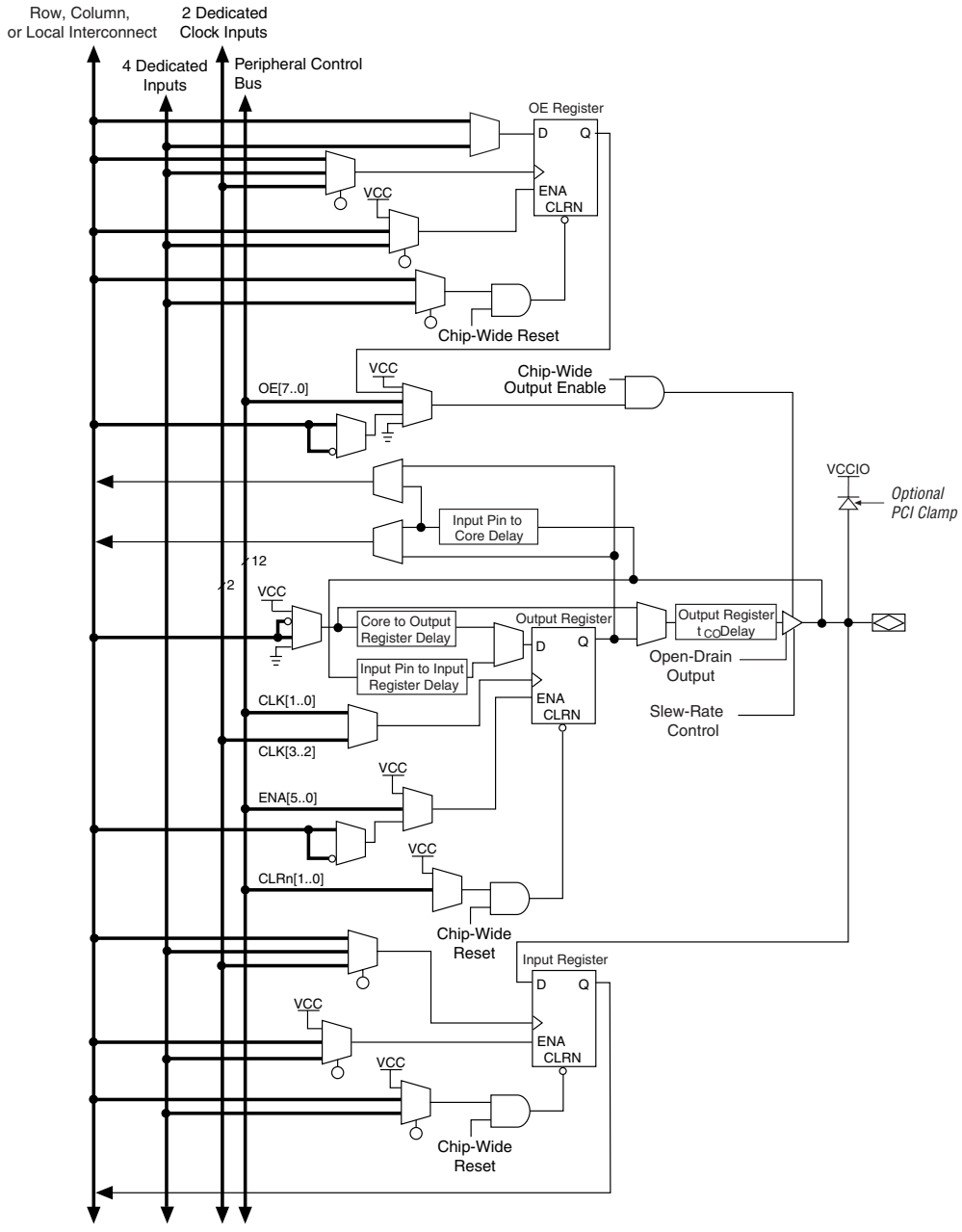
Figure 24. ESB Control Signal Generation



Note to Figure 24:
(1) APEX 20KE devices have four dedicated clocks.

An ESB is fed by the local interconnect, which is driven by adjacent LEs (for high-speed connection to the ESB) or the MegaLAB interconnect. The ESB can drive the local, MegaLAB, or FastTrack Interconnect routing structure to drive LEs and IOEs in the same MegaLAB structure or anywhere in the device.

Figure 25. APEX 20K Bidirectional I/O Registers *Note (1)*



Note to Figure 25:

(1) The output enable and input registers are LE registers in the LAB adjacent to the bidirectional pin.

Notes to Table 16:

(1) To implement the ClockLock and ClockBoost circuitry with the Quartus II software, designers must specify the input frequency. The Quartus II software tunes the PLL in the ClockLock and ClockBoost circuitry to this frequency. The f_{CLKDEV} parameter specifies how much the incoming clock can differ from the specified frequency during device operation. Simulation does not reflect this parameter.

(2) Twenty-five thousand parts per million (PPM) equates to 2.5% of input clock period.

(3) During device configuration, the ClockLock and ClockBoost circuitry is configured before the rest of the device. If the incoming clock is supplied during configuration, the ClockLock and ClockBoost circuitry locks during configuration because the t_{LOCK} value is less than the time required for configuration.

(4) The t_{JITTER} specification is measured under long-term observation.

Tables 17 and 18 summarize the ClockLock and ClockBoost parameters for APEX 20KE devices.

Table 17. APEX 20KE ClockLock & ClockBoost Parameters *Note (1)*

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
t_R	Input rise time				5	ns
t_F	Input fall time				5	ns
t_{INDUTY}	Input duty cycle		40		60	%
$t_{INJITTER}$	Input jitter peak-to-peak				2% of input period	peak-to-peak
$t_{OUTJITTER}$	Jitter on ClockLock or ClockBoost-generated clock				0.35% of output period	RMS
$t_{OUTDUTY}$	Duty cycle for ClockLock or ClockBoost-generated clock		45		55	%
t_{LOCK} *(2), (3)*	Time required for ClockLock or ClockBoost to acquire lock				40	µs

Table 22 shows the JTAG timing parameters and values for APEX 20K devices.

Table 22. APEX 20K JTAG Timing Parameters & Values

Symbol	Parameter	Min	Max	Unit
t_{JCP}	TCK clock period	100		ns
t_{JCH}	TCK clock high time	50		ns
t_{JCL}	TCK clock low time	50		ns
t_{JPSU}	JTAG port setup time	20		ns
t_{JPH}	JTAG port hold time	45		ns
t_{JPCO}	JTAG port clock to output		25	ns
t_{JPZX}	JTAG port high impedance to valid output		25	ns
t_{JPXZ}	JTAG port valid output to high impedance		25	ns
t_{JSSU}	Capture register setup time	20		ns
t_{JSH}	Capture register hold time	45		ns
t_{JSCO}	Update register clock to output		35	ns
t_{JSZX}	Update register high impedance to valid output		35	ns
t_{JSXZ}	Update register valid output to high impedance		35	ns

For more information, see the following documents:

- *Application Note 39 (IEEE Std. 1149.1 (JTAG) Boundary-Scan Testing in Altera Devices)*
- *Jam Programming & Test Language Specification*

Generic Testing

Each APEX 20K device is functionally tested. Complete testing of each configurable static random access memory (SRAM) bit and all logic functionality ensures 100% yield. AC test measurements for APEX 20K devices are made under conditions equivalent to those shown in Figure 32. Multiple test patterns can be used to configure devices during all stages of the production flow.

For DC Operating Specifications on APEX 20KE I/O standards, please refer to *Application Note 117 (Using Selectable I/O Standards in Altera Devices).*

Table 30. APEX 20KE Device Capacitance *Note (15)*

Symbol	Parameter	Conditions	Min	Max	Unit
C_{IN}	Input capacitance	V_{IN} = 0 V, f = 1.0 MHz		8	pF
C_{INCLK}	Input capacitance on dedicated clock pin	V_{IN} = 0 V, f = 1.0 MHz		12	pF
C_{OUT}	Output capacitance	V_{OUT} = 0 V, f = 1.0 MHz		8	pF

Notes to Tables 27 through 30:

(1) See the *Operating Requirements for Altera Devices Data Sheet*.
(2) Minimum DC input is –0.5 V. During transitions, the inputs may undershoot to –2.0 V or overshoot to 5.75 V for input currents less than 100 mA and periods shorter than 20 ns.
(3) Numbers in parentheses are for industrial-temperature-range devices.
(4) Maximum V_{CC} rise time is 100 ms, and V_{CC} must rise monotonically.
(5) Minimum DC input is –0.5 V. During transitions, the inputs may undershoot to –2.0 V or overshoot to the voltage shown in the following table based on input duty cycle for input currents less than 100 mA. The overshoot is dependent upon duty cycle of the signal. The DC case is equivalent to 100% duty cycle.

Vin	Max. Duty Cycle
4.0V	100% (DC)
4.1	90%
4.2	50%
4.3	30%
4.4	17%
4.5	10%

(6) All pins, including dedicated inputs, clock, I/O, and JTAG pins, may be driven before V_{CCINT} and V_{CCIO} are powered.
(7) Typical values are for T_A = 25° C, V_{CCINT} = 1.8 V, and V_{CCIO} = 1.8 V, 2.5 V or 3.3 V.
(8) These values are specified under the APEX 20KE device recommended operating conditions, shown in Table 24 on page 60.
(9) Refer to *Application Note 117 (Using Selectable I/O Standards in Altera Devices)* for the V_{IH}, V_{IL}, V_{OH}, V_{OL}, and I_I parameters when VCCIO = 1.8 V.
(10) The APEX 20KE input buffers are compatible with 1.8-V, 2.5-V and 3.3-V (LVTTL and LVCMOS) signals. Additionally, the input buffers are 3.3-V PCI compliant. Input buffers also meet specifications for GTL+, CTT, AGP, SSTL-2, SSTL-3, and HSTL.
(11) The I_{OH} parameter refers to high-level TTL, PCI, or CMOS output current.
(12) The I_{OL} parameter refers to low-level TTL, PCI, or CMOS output current. This parameter applies to open-drain pins as well as output pins.
(13) This value is specified for normal device operation. The value may vary during power-up.
(14) Pin pull-up resistance values will be lower if an external source drives the pin higher than V_{CCIO}.
(15) Capacitance is sample-tested only.

Figure 33 shows the relationship between V_{CCIO} and V_{CCINT} for 3.3-V PCI compliance on APEX 20K devices.

Figure 33. Relationship between V_{CCIO} & V_{CCINT} for 3.3-V PCI Compliance

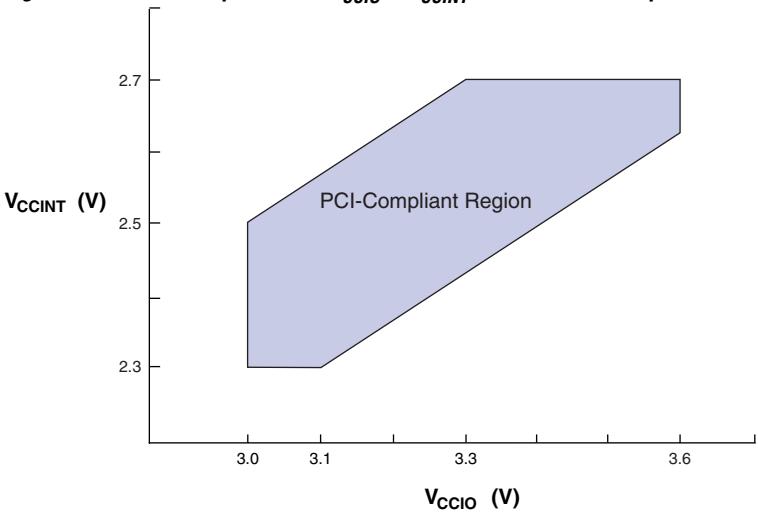
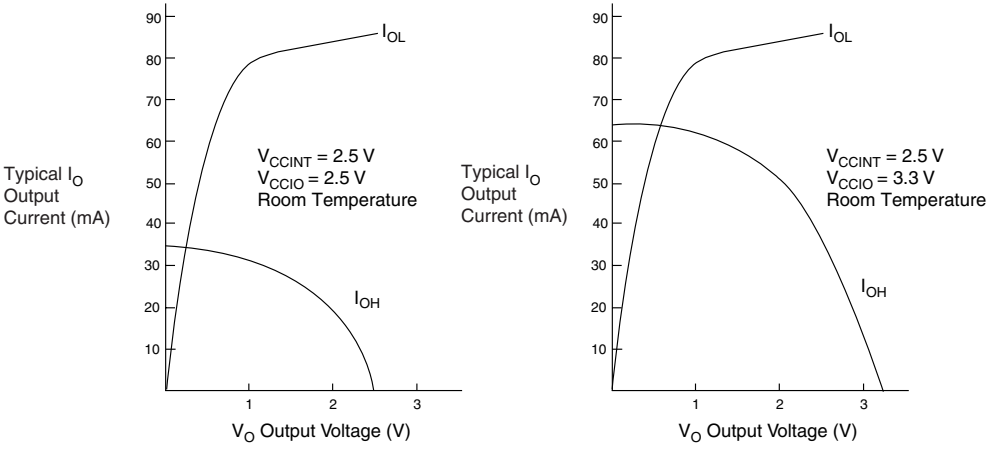


Figure 34 shows the typical output drive characteristics of APEX 20K devices with 3.3-V and 2.5-V V_{CCIO}. The output driver is compatible with the 3.3-V ***PCI Local Bus Specification, Revision 2.2*** (when VCCIO pins are connected to 3.3 V). 5-V tolerant APEX 20K devices in the -1 speed grade are 5-V PCI compliant over all operating conditions.

Figure 34. Output Drive Characteristics of APEX 20K Device *Note (1)*



Note to Figure 34:
(1) These are transient (AC) currents.

Table 31. APEX 20K f_{MAX} Timing Parameters (Part 2 of 2)	
Symbol	**Parameter**
$t_{ESBDATACO2}$	ESB clock-to-output delay without output registers
t_{ESBDD}	ESB data-in to data-out delay for RAM mode
t_{PD}	ESB macrocell input to non-registered output
$t_{PTERMSU}$	ESB macrocell register setup time before clock
$t_{PTERMCO}$	ESB macrocell register clock-to-output delay
t_{F1-4}	Fanout delay using local interconnect
t_{F5-20}	Fanout delay using MegaLab Interconnect
t_{F20+}	Fanout delay using FastTrack Interconnect
t_{CH}	Minimum clock high time from clock pin
t_{CL}	Minimum clock low time from clock pin
t_{CLRP}	LE clear pulse width
t_{PREP}	LE preset pulse width
t_{ESBCH}	Clock high time
t_{ESBCL}	Clock low time
t_{ESBWP}	Write pulse width
t_{ESBRP}	Read pulse width

Tables 32 and 33 describe APEX 20K external timing parameters.

Table 32. APEX 20K External Timing Parameters *Note (1)*	
Symbol	**Clock Parameter**
t_{INSU}	Setup time with global clock at IOE register
t_{INH}	Hold time with global clock at IOE register
t_{OUTCO}	Clock-to-output delay with global clock at IOE register

Table 33. APEX 20K External Bidirectional Timing Parameters *Note (1)*		
Symbol	**Parameter**	**Conditions**
$t_{INSUBIDIR}$	Setup time for bidirectional pins with global clock at same-row or same-column LE register	
$t_{INHBIDIR}$	Hold time for bidirectional pins with global clock at same-row or same-column LE register	
$t_{OUTCOBIDIR}$	Clock-to-output delay for bidirectional pins with global clock at IOE register	C1 = 10 pF
$t_{XZBIDIR}$	Synchronous IOE output buffer disable delay	C1 = 10 pF
$t_{ZXBIDIR}$	Synchronous IOE output buffer enable delay, slow slew rate = off	C1 = 10 pF

Table 43. EP20K100 External Timing Parameters

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{INSU} (1)	2.3		2.8		3.2		ns
t_{INH} (1)	0.0		0.0		0.0		ns
t_{OUTCO} (1)	2.0	4.5	2.0	4.9	2.0	6.6	ns
t_{INSU} (2)	1.1		1.2		–		ns
t_{INH} (2)	0.0		0.0		–		ns
t_{OUTCO} (2)	0.5	2.7	0.5	3.1	–	4.8	ns

Table 44. EP20K100 External Bidirectional Timing Parameters

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
$t_{INSUBIDIR}$ (1)	2.3		2.8		3.2		ns
$t_{INHBIDIR}$ (1)	0.0		0.0		0.0		ns
$t_{OUTCOBIDIR}$ (1)	2.0	4.5	2.0	4.9	2.0	6.6	ns
$t_{XZBIDIR}$ (1)		5.0		5.9		6.9	ns
$t_{ZXBIDIR}$ (1)		5.0		5.9		6.9	ns
$t_{INSUBIDIR}$ (2)	1.0		1.2		–		ns
$t_{INHBIDIR}$ (2)	0.0		0.0		–		ns
$t_{OUTCOBIDIR}$ (2)	0.5	2.7	0.5	3.1	–	–	ns
$t_{XZBIDIR}$ (2)		4.3		5.0		–	ns
$t_{ZXBIDIR}$ (2)		4.3		5.0		–	ns

Table 45. EP20K200 External Timing Parameters

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{INSU} (1)	1.9		2.3		2.6		ns
t_{INH} (1)	0.0		0.0		0.0		ns
t_{OUTCO} (1)	2.0	4.6	2.0	5.6	2.0	6.8	ns
t_{INSU} (2)	1.1		1.2		–		ns
t_{INH} (2)	0.0		0.0		–		ns
t_{OUTCO} (2)	0.5	2.7	0.5	3.1	–	–	ns

Table 62. EP20K100E f_{MAX} ESB Timing Microparameters

Symbol	-1		-2		-3		Unit
	Min	Max	Min	Max	Min	Max	
t_{ESBARC}		1.61		1.84		1.97	ns
t_{ESBSRC}		2.57		2.97		3.20	ns
t_{ESBAWC}		0.52		4.09		4.39	ns
t_{ESBSWC}		3.17		3.78		4.09	ns
$t_{ESBWASU}$	0.56		6.41		0.63		ns
t_{ESBWAH}	0.48		0.54		0.55		ns
$t_{ESBWDSU}$	0.71		0.80		0.81		ns
t_{ESBWDH}	.048		0.54		0.55		ns
$t_{ESBRASU}$	1.57		1.75		1.87		ns
t_{ESBRAH}	0.00		0.00		0.20		ns
$t_{ESBWESU}$	1.54		1.72		1.80		ns
t_{ESBWEH}	0.00		0.00		0.00		ns
$t_{ESBDATASU}$	-0.16		-0.20		-0.20		ns
$t_{ESBDATAH}$	0.13		0.13		0.13		ns
$t_{ESBWADDRSU}$	0.12		0.08		0.13		ns
$t_{ESBRADDRSU}$	0.17		0.15		0.19		ns
$t_{ESBDATACO1}$		1.20		1.39		1.52	ns
$t_{ESBDATACO2}$		2.54		2.99		3.22	ns
t_{ESBDD}		3.06		3.56		3.85	ns
t_{PD}		1.73		2.02		2.20	ns
$t_{PTERMSU}$	1.11		1.26		1.38		ns
$t_{PTERMCO}$		1.19		1.40		1.08	ns

Table 63. EP20K100E f_{MAX} Routing Delays

Symbol	-1		-2		-3		Unit
	Min	Max	Min	Max	Min	Max	
t_{F1-4}		0.24		0.27		0.29	ns
t_{F5-20}		1.04		1.26		1.52	ns
t_{F20+}		1.12		1.36		1.86	ns

Table 76. EP20K200E Minimum Pulse Width Timing Parameters

Symbol	-1		-2		-3		Unit
	Min	Max	Min	Max	Min	Max	
t_{CH}	1.36		2.44		2.65		ns
t_{CL}	1.36		2.44		2.65		ns
t_{CLRP}	0.18		0.19		0.21		ns
t_{PREP}	0.18		0.19		0.21		ns
t_{ESBCH}	1.36		2.44		2.65		ns
t_{ESBCL}	1.36		2.44		2.65		ns
t_{ESBWP}	1.18		1.48		1.76		ns
t_{ESBRP}	0.95		1.17		1.41		ns

Table 77. EP20K200E External Timing Parameters

Symbol	-1		-2		-3		Unit
	Min	Max	Min	Max	Min	Max	
t_{INSU}	2.24		2.35		2.47		ns
t_{INH}	0.00		0.00		0.00		ns
t_{OUTCO}	2.00	5.12	2.00	5.62	2.00	6.11	ns
$t_{INSUPLL}$	2.13		2.07		-		ns
t_{INHPLL}	0.00		0.00		-		ns
$t_{OUTCOPLL}$	0.50	3.01	0.50	3.36	-	-	ns

Table 90. EP20K400E External Bidirectional Timing Parameters

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
$t_{INSUBIDIR}$	2.93		3.23		3.44		ns
$t_{INHBIDIR}$	0.00		0.00		0.00		ns
$t_{OUTCOBIDIR}$	2.00	5.25	2.00	5.79	2.00	6.32	ns
$t_{XZBIDIR}$		5.95		6.77		7.12	ns
$t_{ZXBIDIR}$		5.95		6.77		7.12	ns
$t_{INSUBIDIRPLL}$	4.31		4.76		-		ns
$t_{INHBIDIRPLL}$	0.00		0.00		-		ns
$t_{OUTCOBIDIRPLL}$	0.50	2.25	0.50	2.45	-	-	ns
$t_{XZBIDIRPLL}$		2.94		3.43		-	ns
$t_{ZXBIDIRPLL}$		2.94		3.43		-	ns

Tables 91 through 96 describe f_{MAX} LE Timing Microparameters, f_{MAX} ESB Timing Microparameters, f_{MAX} Routing Delays, Minimum Pulse Width Timing Parameters, External Timing Parameters, and External Bidirectional Timing Parameters for EP20K600E APEX 20KE devices.

Table 91. EP20K600E f_{MAX} LE Timing Microparameters

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{SU}	0.16		0.16		0.17		ns
t_{H}	0.29		0.33		0.37		ns
t_{CO}		0.65		0.38		0.49	ns
t_{LUT}		0.70		1.00		1.30	ns

Table 92. EP20K600E f_{MAX} ESB Timing Microparameters

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{ESBARC}		1.67		2.39		3.11	ns
t_{ESBSRC}		2.27		3.07		3.86	ns
t_{ESBAWC}		3.19		4.56		5.93	ns
t_{ESBSWC}		3.51		4.62		5.72	ns
$t_{ESBWASU}$	1.46		2.08		2.70		ns
t_{ESBWAH}	0.00		0.00		0.00		ns
$t_{ESBWDSU}$	1.60		2.29		2.97		ns
t_{ESBWDH}	0.00		0.00		0.00		ns
$t_{ESBRASU}$	1.61		2.30		2.99		ns
t_{ESBRAH}	0.00		0.00		0.00		ns
$t_{ESBWESU}$	1.49		2.30		3.11		ns
t_{ESBWEH}	0.00		0.00		0.00		ns
$t_{ESBDATASU}$	-0.01		0.35		0.71		ns
$t_{ESBDATAH}$	0.13		0.13		0.13		ns
$t_{ESBWADDRSU}$	0.19		0.62		1.06		ns
$t_{ESBRADDRSU}$	0.25		0.71		1.17		ns
$t_{ESBDATACO1}$		1.01		1.19		1.37	ns
$t_{ESBDATACO2}$		2.18		3.12		4.05	ns
t_{ESBDD}		3.19		4.56		5.93	ns
t_{PD}		1.57		2.25		2.92	ns
$t_{PTERMSU}$	0.85		1.43		2.01		ns
$t_{PTERMCO}$		1.03		1.21		1.39	ns

Table 93. EP20K600E f_{MAX} Routing Delays

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{F1-4}		0.22		0.25		0.26	ns
t_{F5-20}		1.26		1.39		1.52	ns
t_{F20+}		3.51		3.88		4.26	ns

Table 106. EP20K1500E Minimum Pulse Width Timing Parameters

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{CH}	1.25		1.43		1.67		ns
t_{CL}	1.25		1.43		1.67		ns
t_{CLRP}	0.20		0.20		0.20		ns
t_{PREP}	0.20		0.20		0.20		ns
t_{ESBCH}	1.25		1.43		1.67		ns
t_{ESBCL}	1.25		1.43		1.67		ns
t_{ESBWP}	1.28		1.51		1.65		ns
t_{ESBRP}	1.11		1.29		1.41		ns

Table 107. EP20K1500E External Timing Parameters

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{INSU}	3.09		3.30		3.58		ns
t_{INH}	0.00		0.00		0.00		ns
t_{OUTCO}	2.00	6.18	2.00	6.81	2.00	7.36	ns
$t_{INSUPLL}$	1.94		2.08		-		ns
t_{INHPLL}	0.00		0.00		-		ns
$t_{OUTCOPLL}$	0.50	2.67	0.50	2.99	-	-	ns

Table 110. Selectable I/O Standard Output Delays

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	Min
LVCMOS		0.00		0.00		0.00	ns
LVTTL		0.00		0.00		0.00	ns
2.5 V		0.00		0.09		0.10	ns
1.8 V		2.49		2.98		3.03	ns
PCI		–0.03		0.17		0.16	ns
GTL+		0.75		0.75		0.76	ns
SSTL-3 Class I		1.39		1.51		1.50	ns
SSTL-3 Class II		1.11		1.23		1.23	ns
SSTL-2 Class I		1.35		1.48		1.47	ns
SSTL-2 Class II		1.00		1.12		1.12	ns
LVDS		–0.48		–0.48		–0.48	ns
CTT		0.00		0.00		0.00	ns
AGP		0.00		0.00		0.00	ns

Power Consumption

To estimate device power consumption, use the interactive power calculator on the Altera web site at **http://www.altera.com**.

Configuration & Operation

The APEX 20K architecture supports several configuration schemes. This section summarizes the device operating modes and available device configuration schemes.

Operating Modes

The APEX architecture uses SRAM configuration elements that require configuration data to be loaded each time the circuit powers up. The process of physically loading the SRAM data into the device is called configuration. During initialization, which occurs immediately after configuration, the device resets registers, enables I/O pins, and begins to operate as a logic device. The I/O pins are tri-stated during power-up, and before and during configuration. Together, the configuration and initialization processes are called *command mode*; normal device operation is called *user mode*.

Before and during device configuration, all I/O pins are pulled to V_{CCIO} by a built-in weak pull-up resistor.